80-M112PMA010M7-K209A70
datasheet

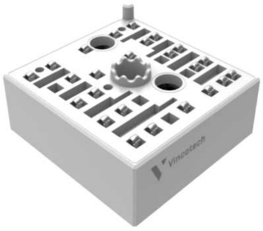
Vincotech

MiniSKiiP® PIM 1 | **1200 V / 10 A**

Features

- IGBT M7 with low V_{CEsat} and improved EMC behavior
- Open emitter configuration
- Solder-free spring contact technology
- Built-in PTC

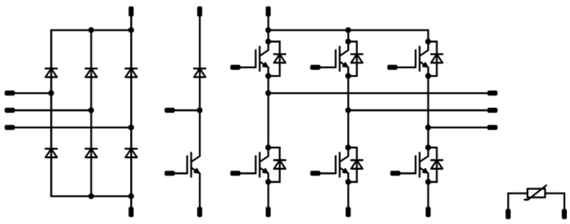
MiniSkiip® 1 housing



Target applications

- Industrial Drives

Schematic



Types

- 80-M112PMA010M7-K209A70

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Rectifier Diode				
Peak Repetitive Reverse Voltage	V_{RRM}		1600	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ T_s = 80 °C	35	A
Surge (non-repetitive) forward current	I_{FSM}	50 Hz Single Half Sine Wave t_p = 10 ms T_j = 150 °C	200	A
Surge current capability	I^2t	50 Hz Single Half Sine Wave t_p = 10 ms T_j = 150 °C	200	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	51	W
Maximum Junction Temperature	T_{jmax}		150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Inverter Switch					
Collector-emitter voltage	V_{CES}			1200	V
Collector current	I_C	$T_j = T_{jmax}$	T_s = 80 °C	14	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	67	W
Gate-emitter voltage	V_{GES}			±20	V
Maximum junction temperature	T_{jmax}			175	°C
Inverter Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$	T_s = 80 °C	14	A
Repetitive peak forward current	I_{FRM}			20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	53	W
Maximum junction temperature	T_{jmax}			175	°C
Brake Switch					
Collector-emitter voltage	V_{CES}			1200	V
Collector current	I_C	$T_j = T_{jmax}$	T_s = 80 °C	14	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	67	W
Gate-emitter voltage	V_{GES}			±20	V
Maximum junction temperature	T_{jmax}			175	°C
Brake Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$	T_s = 80 °C	14	A
Repetitive peak forward current	I_{FRM}			20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	53	W
Maximum junction temperature	T_{jmax}			175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Module Properties					
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	5500	V
		AC Voltage	t_p = 1 min	2500	V
Creepage distance		With std lid For more information see handling instructions		6,3	mm
Clearance		With std lid For more information see handling instructions		6,3	mm
Comparative Tracking Index	CTI			> 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	**Min**	**Typ**	**Max**	
Rectifier Diode										
Static										
Forward voltage	V_F				25	25 125		1,22 1,21	1,75	V
Reverse leakage current	I_r			1600		25 145			50 1100	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 2,5 W/mK (HPTP)						1,37		K/W

Vincotech

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}$			0,001	25	5,4	6	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		10	25 125 150		1,65 1,90 1,95	1,95	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			55	µA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}		0	10		25		2000		pF
Output capacitance	C_{oes}		0	10		25		86		pF
Reverse transfer capacitance	C_{res}		0	10		25		23		pF
Gate charge	Q_g		15	600	10	25		80		nC
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 2,5 W/mK (HPTP)						1,41		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{goff} = 32 Ω R_{gon} = 32 Ω	±15	600	10	25 125 150		128 126 123		ns
Rise time	t_r	R_{goff} = 32 Ω R_{gon} = 32 Ω	±15	600	10	25 125 150		29 32 34		ns
Turn-off delay time	$t_{d(off)}$	R_{goff} = 32 Ω R_{gon} = 32 Ω	±15	600	10	25 125 150		145 179 182		ns
Fall time	t_f	R_{goff} = 32 Ω R_{gon} = 32 Ω	±15	600	10	25 125 150		98 108 117		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD} = 1,1 µC Q_{rFWD} = 1,7 µC Q_{rFWD} = 1,8 µC	±15	600	10	25 125 150		0,883 1,125 1,189		mWs
Turn-off energy (per pulse)	E_{off}		±15	600	10	25 125 150		0,656 0,860 0,908		mWs

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_F				10	25 125 150		1,61 1,69 1,69	2,1	V
Reverse leakage current	I_R			1200		25			25	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 2,5 W/mK (HPTP)						1,80		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt = 278 A/µs di/dt = 270 A/µs di/dt = 272 A/µs	±15	600	10	25 125 150		9 9 9		A
Reverse recovery time	t_{rr}					25 125 150		254 373 409		ns
Recovered charge	Q_r					25 125 150		1,088 1,664 1,808		µC
Reverse recovered energy	E_{rec}					25 125 150		0,374 0,620 0,680		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		85 54 49		A/µs

Vincotech

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Brake Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}$			0,001	25	5,4	6	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		10	25 125 150		1,65 1,90 1,95	1,95	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			55	µA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}		0	10		25		2000		pF
Output capacitance	C_{oes}		0	10		25		86		pF
Reverse transfer capacitance	C_{res}		0	10		25		23		pF
Gate charge	Q_g		15	600	10	25		80		nC
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 2,5 W/mK (HPTP)						1,41		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{goff} = 32 Ω R_{gon} = 32 Ω	15/0	600	10	25 125 150		72 68 68		ns
Rise time	t_r	R_{goff} = 32 Ω R_{gon} = 32 Ω	15/0	600	10	25 125 150		46 50 50		ns
Turn-off delay time	$t_{d(off)}$	R_{goff} = 32 Ω R_{gon} = 32 Ω	15/0	600	10	25 125 150		225 251 257		ns
Fall time	t_f	R_{goff} = 32 Ω R_{gon} = 32 Ω	15/0	600	10	25 125 150		93 111 113		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD} = 1 µC Q_{rFWD} = 1,6 µC Q_{rFWD} = 1,8 µC	15/0	600	10	25 125 150		0,973 1,253 1,332		mWs
Turn-off energy (per pulse)	E_{off}		15/0	600	10	25 125 150		0,647 0,863 0,916		mWs

Characteristic Values

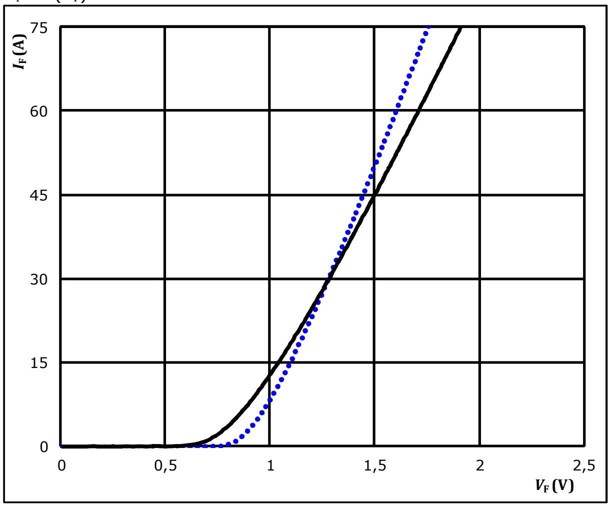
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Diode										
Static										
Forward voltage	V_F				10	25 125 150		1,61 1,69 1,69	2,1	V
Reverse leakage current	I_R			1200		25			25	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 2,5 W/mK (HPTP)						1,80		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt = 165 A/µs di/dt = 148 A/µs di/dt = 153 A/µs	15/0	600	10	25 125 150		7 8 8		A
Reverse recovery time	t_{rr}					25 125 150		265 396 448		ns
Recovered charge	Q_r					25 125 150		0,989 1,568 1,773		µC
Reverse recovered energy	E_{rec}					25 125 150		0,337 0,577 0,666		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		59 41 35		A/µs
Thermistor										
Rated resistance	R					25		1		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1670 Ω				100	-2		+2	%
R_{100}	R					100		1670		Ω
Power dissipation constant						25		0,76		mW/K
A-value	$A_{(25/50)}$					25		$7,635 \cdot 10^{-3}$		1/K
B-value	$B_{(25/100)}$					25		$1,731 \cdot 10^{-5}$		1/K²
Vincotech PTC Reference									E	

Rectifier Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



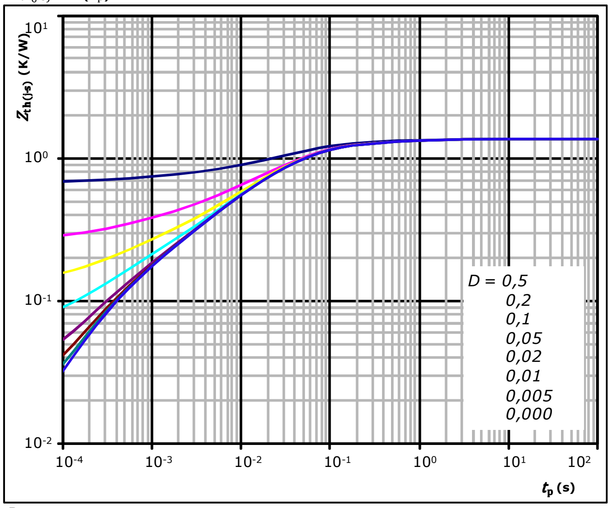
t_p = 250 μs

T_j: 25 °C (dotted), 125 °C (solid)

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,37 K/W

Diode thermal model values

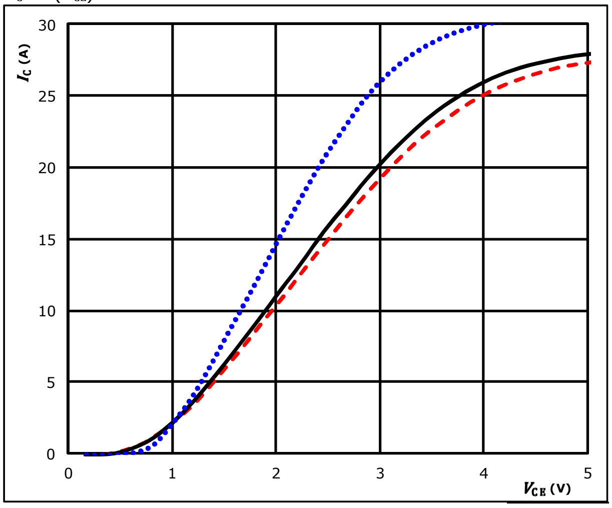
R (K/W)	τ (s)
6,75E-02	1,56E+00
1,34E-01	2,41E-01
6,34E-01	4,40E-02
3,25E-01	9,85E-03
1,24E-01	2,12E-03
8,72E-02	3,56E-04
8,72E-02	3,56E-04

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

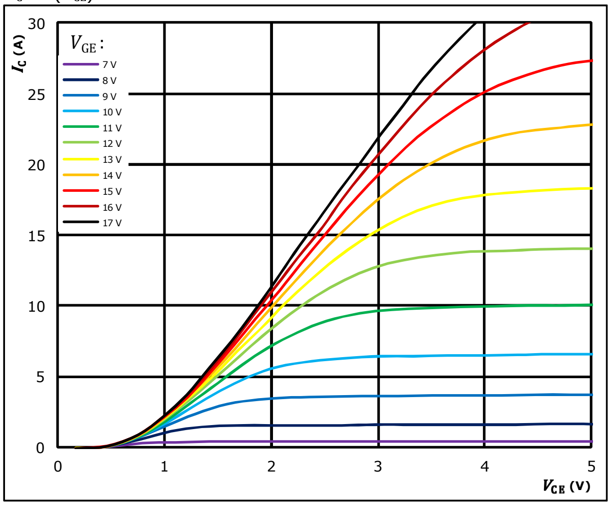


t_p =	250	µs		25 °C	·········
V_{GE} =	15	V	T_j:	125 °C	——
				150 °C	- - -

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$



t_p = 250 µs

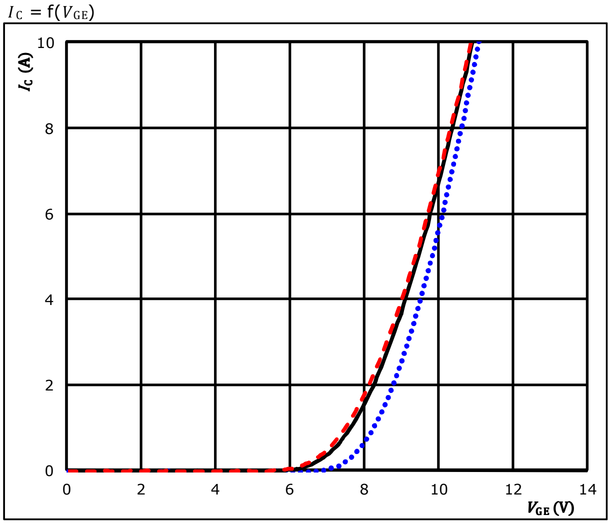
T_j = 150 °C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

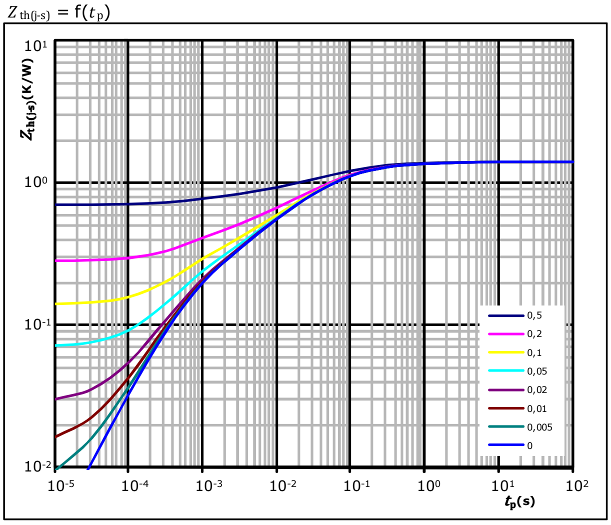


t_p =	100	µs		25 °C	·········
V_{CE} =	10	V	T_j:	125 °C	——
				150 °C	- - -

figure 4. **IGBT**

Transient thermal impedance as function of pulse duration

$Z_{th(j\text{-}s)} = f(t_p)$



D = t_p / T

$R_{th(j\text{-}s)}$ = 1,41 K/W

IGBT thermal model values

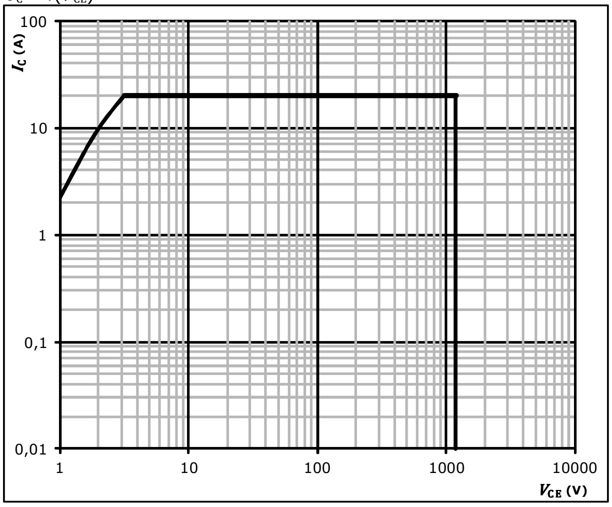
R (K/W)	τ (s)
6,61E-02	1,89E+00
1,81E-01	2,00E-01
5,32E-01	4,93E-02
3,21E-01	1,08E-02
1,59E-01	2,58E-03
1,49E-01	4,46E-04

Inverter Switch Characteristics

figure 5. **IGBT**

Safe operating area

$I_C = f(V_{CE})$



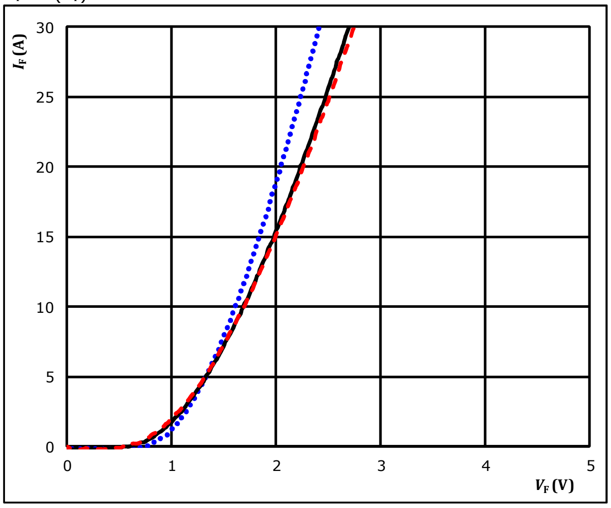
D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

Inverter Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



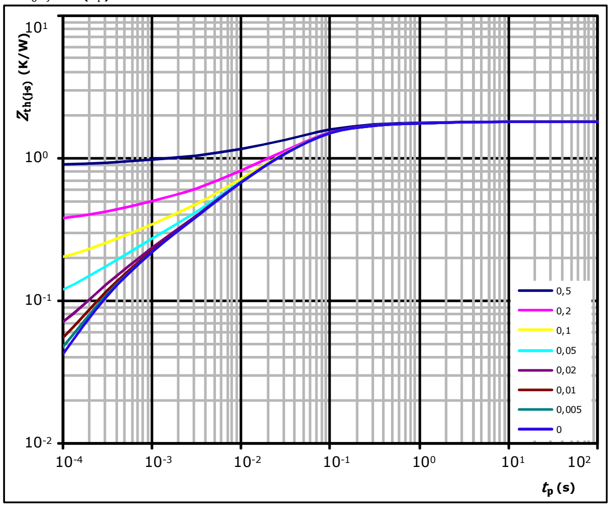
t_p = 250 μs

T_j:
25 °C
125 °C
150 °C

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 1,80 K/W

FWD thermal model values

R (K/W)	τ (s)
9,72E-02	1,16E+00
2,38E-01	1,67E-01
9,04E-01	4,46E-02
3,13E-01	8,53E-03
1,25E-01	2,30E-03
1,19E-01	3,66E-04

80-M112PMA010M7-K209A70
datasheet

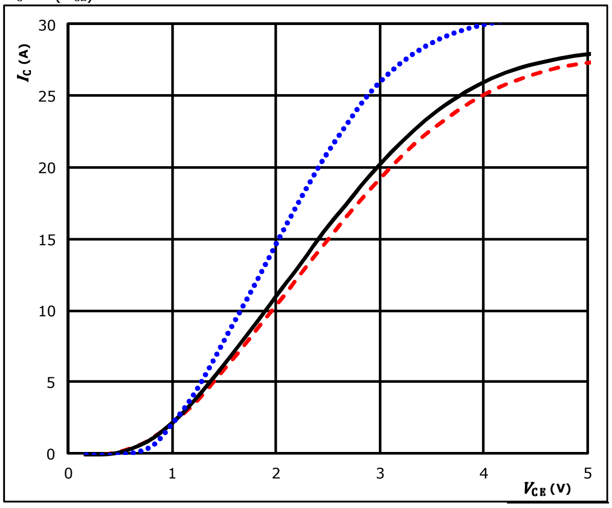
Vincotech

Brake Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

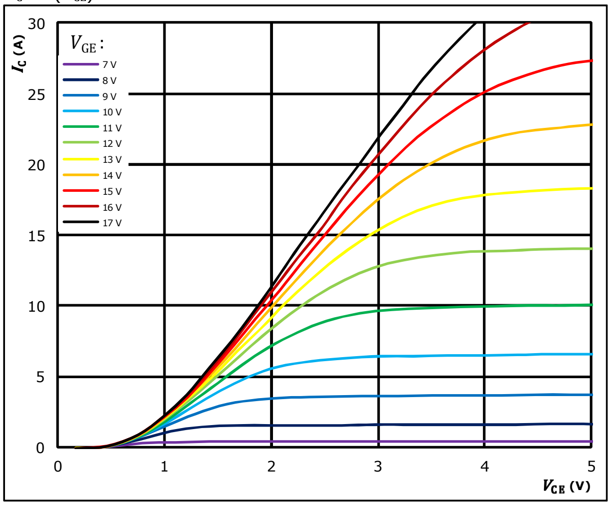


t_p =	250	µs		25 °C	············
V_{GE} =	15	V	T_j:	125 °C	———
				150 °C	– – – –

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$



t_p = 250 µs

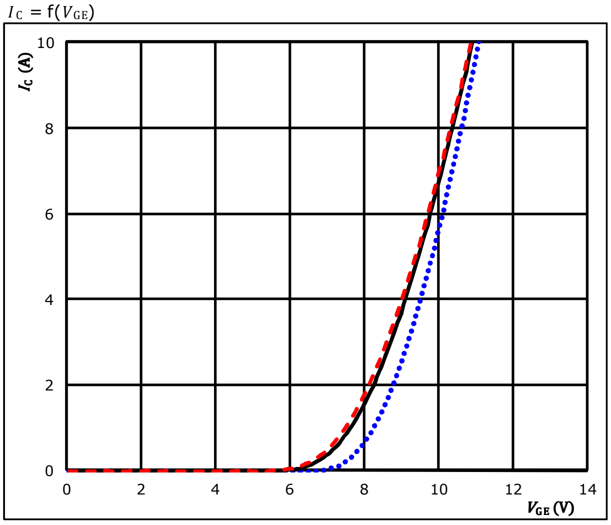
T_j = 150 °C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

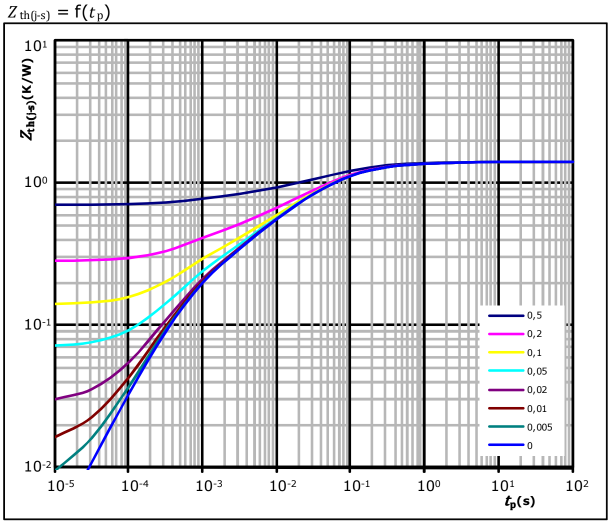


t_p =	100	µs		25 °C	············
V_{CE} =	10	V	T_j:	125 °C	———
				150 °C	– – – –

figure 4. **IGBT**

Transient thermal impedance as function of pulse duration

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,41 K/W

IGBT thermal model values

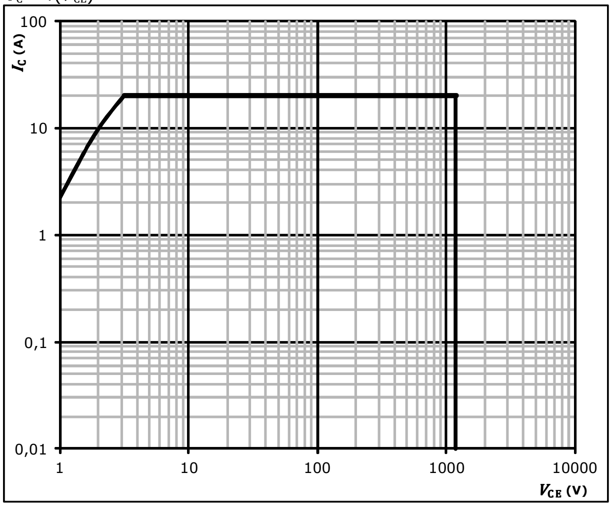
R (K/W)	τ (s)
6,61E-02	1,89E+00
1,81E-01	2,00E-01
5,32E-01	4,93E-02
3,21E-01	1,08E-02
1,59E-01	2,58E-03
1,49E-01	4,46E-04

Brake Switch Characteristics

figure 5. **IGBT**

Safe operating area

$I_C = f(V_{CE})$



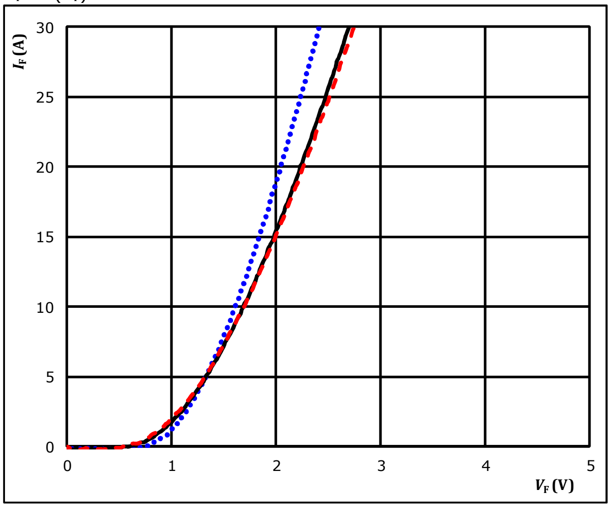
D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

Brake Diode Characteristics

figure 1.	**FWD**

Typical forward characteristics

$I_F = f(V_F)$



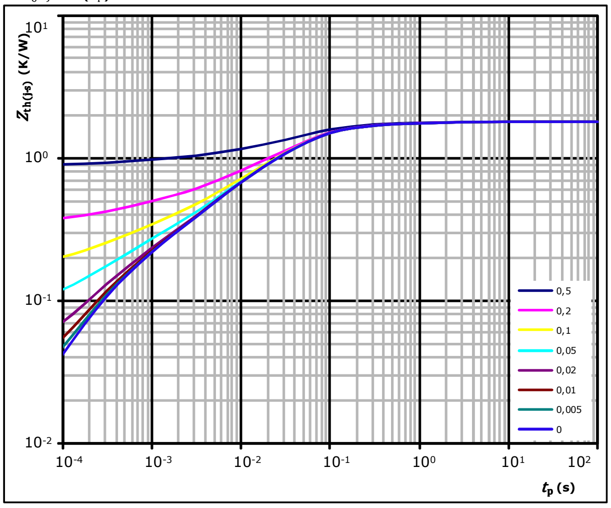
t_p = 250 µs

T_j: 25 °C; 125 °C; 150 °C

figure 2.	**FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j\text{-}s)} = f(t_p)$



$D = t_p / T$

$R_{th(j\text{-}s)}$ = 1,80 K/W

FWD thermal model values

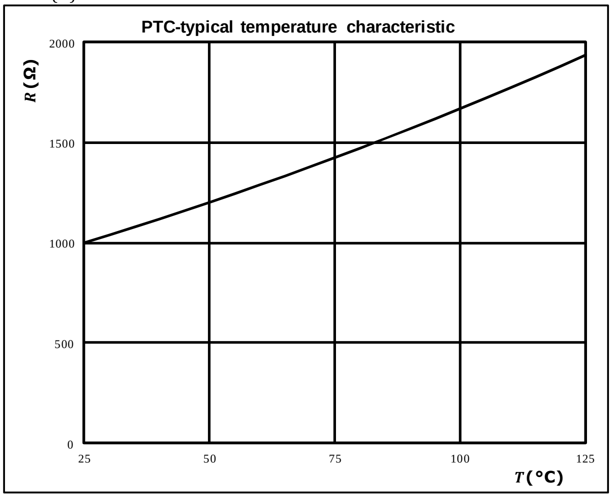
R (K/W)	τ (s)
9,72E-02	1,16E+00
2,38E-01	1,67E-01
9,04E-01	4,46E-02
3,13E-01	8,53E-03
1,25E-01	2,30E-03
1,19E-01	3,66E-04

Thermistor Characteristics

figure 1.	**Thermistor**

Typical PTC characteristic as a function of temperature

$R = f(T)$

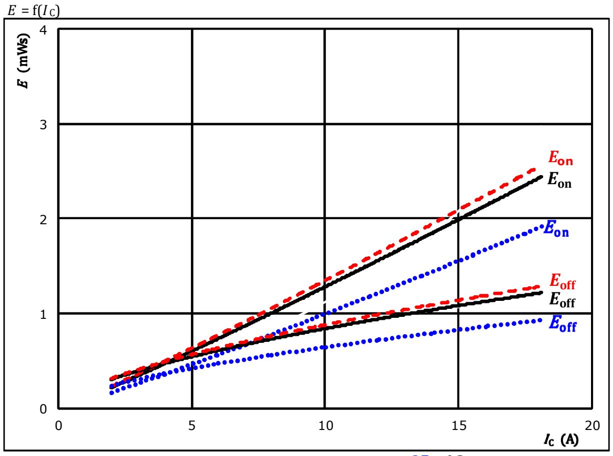


Inverter Switching Characteristics

figure 1. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



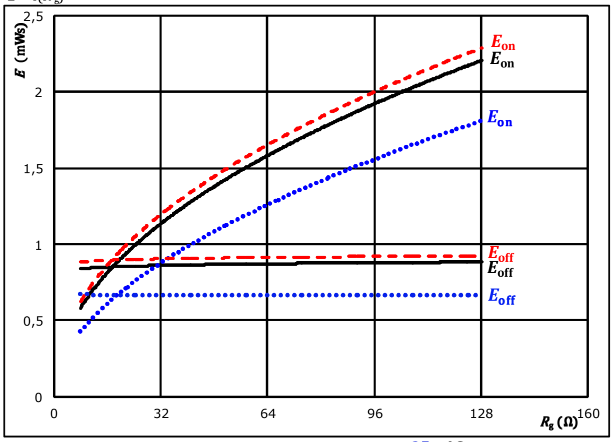
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	··········
V_{GE} =	±15	V		125 °C	———
R_{gon} =	32	Ω		150 °C	– – –
R_{goff} =	32	Ω			

figure 2. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



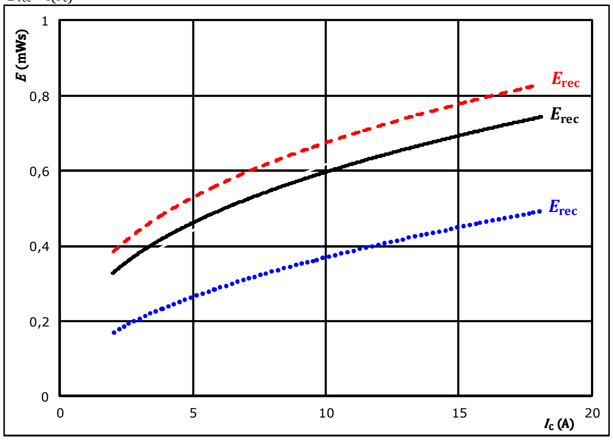
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	··········
V_{GE} =	±15	V		125 °C	———
I_C =	10	A		150 °C	– – –

figure 3. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



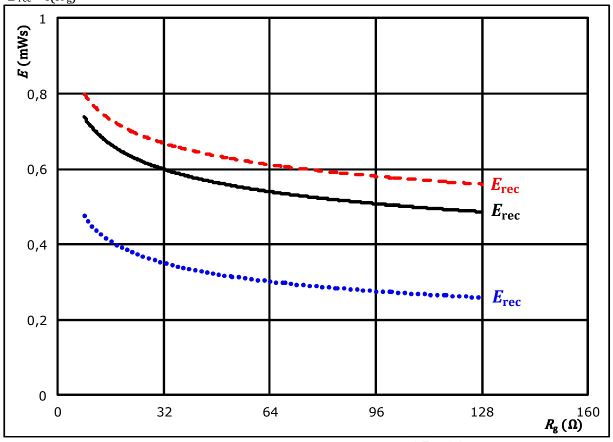
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	··········
V_{GE} =	±15	V		125 °C	———
R_{gon} =	32	Ω		150 °C	– – –

figure 4. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

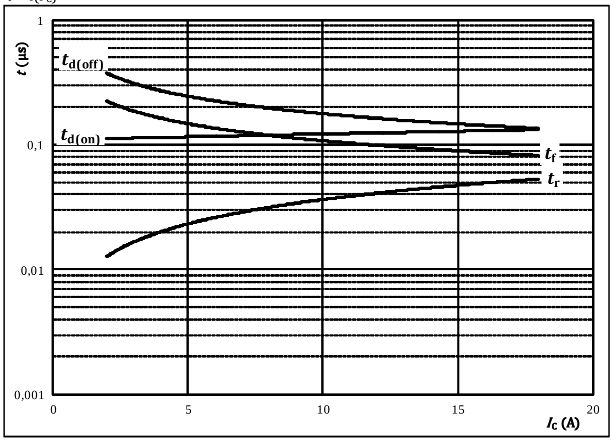
V_{CE} =	600	V	T_j:	25 °C	··········
V_{GE} =	±15	V		125 °C	———
I_C =	10	A		150 °C	– – –

Inverter Switching Characteristics

figure 5. IGBT

Typical switching times as a function of collector current

$t = f(I_C)$



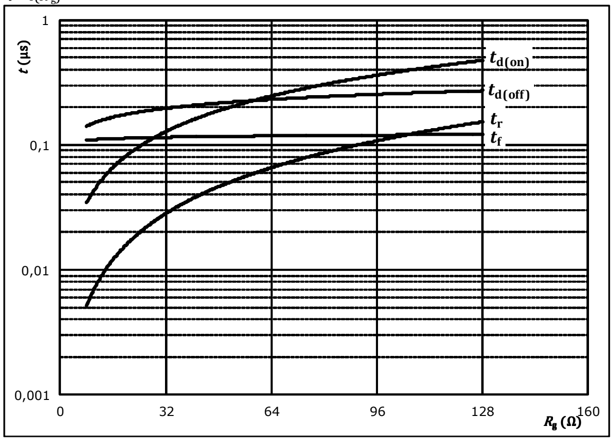
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω
R_{goff} =	32	Ω

figure 6. IGBT

Typical switching times as a function of gate resistor

$t = f(R_g)$



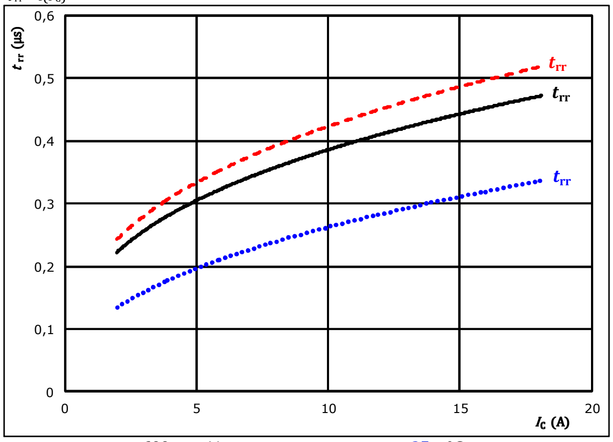
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	10	A

figure 7. FWD

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$

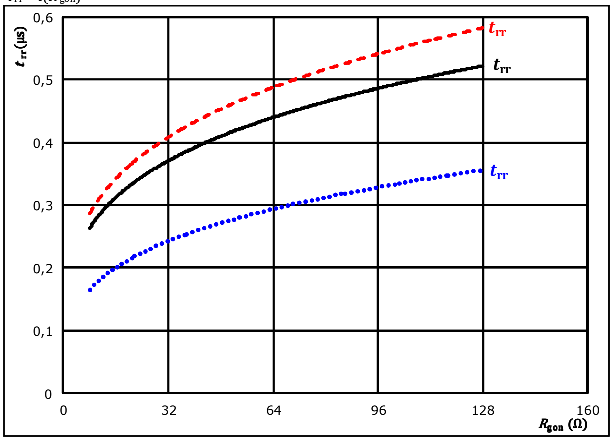


At					
V_{CE} =	600	V		25 °C	dotted
V_{GE} =	±15	V	T_j:	125 °C	solid
R_{gon} =	32	Ω		150 °C	dashed

figure 8. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



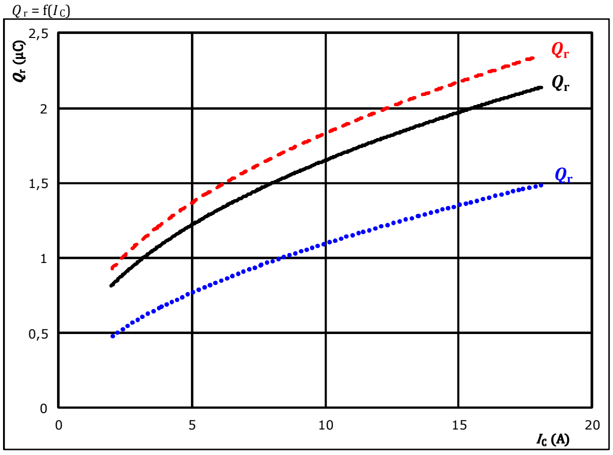
At					
V_{CE} =	600	V		25 °C	dotted
V_{GE} =	±15	V	T_j:	125 °C	solid
I_C =	10	A		150 °C	dashed

Inverter Switching Characteristics

figure 9. FWD

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$

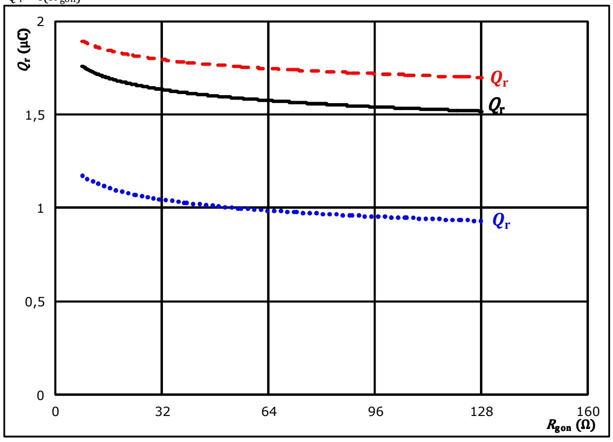


At					
V_{CE} =	600	V	T_j:	25 °C	dotted
V_{GE} =	±15	V		125 °C	solid
R_{gon} =	32	Ω		150 °C	dashed

figure 10. FWD

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$

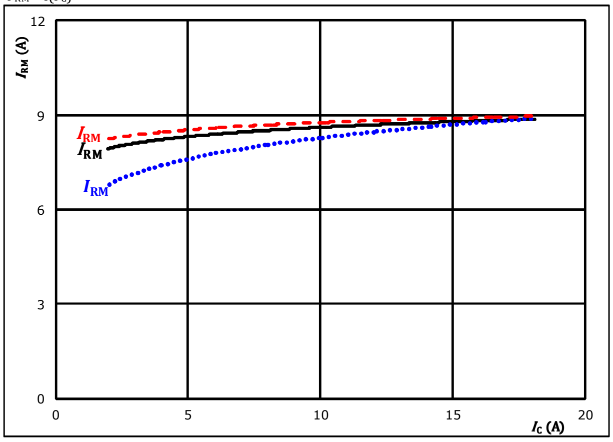


At					
V_{CE} =	600	V	T_j:	25 °C	dotted
V_{GE} =	±15	V		125 °C	solid
I_C =	10	A		150 °C	dashed

figure 11. FWD

Typical peak reverse recovery current current as a function of collector current

$I_{RM} = f(I_C)$

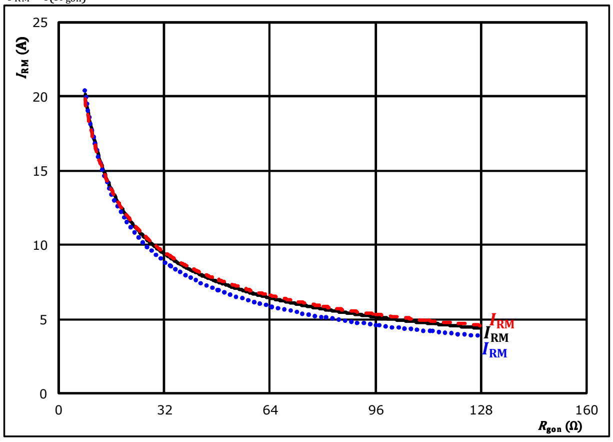


At					
V_{CE} :	600	V	T_j:	25 °C	dotted
V_{GE} =	±15	V		125 °C	solid
R_{gon} =	32	Ω		150 °C	dashed

figure 12. FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



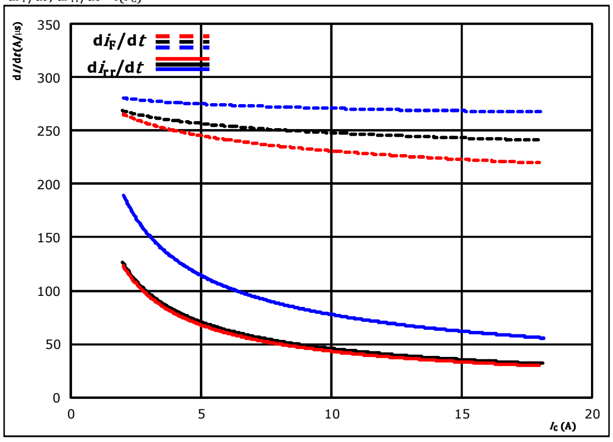
At					
V_{CE} =	600	V	T_j:	25 °C	dotted
V_{GE} =	±15	V		125 °C	solid
I_C =	10	A		150 °C	dashed

Inverter Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



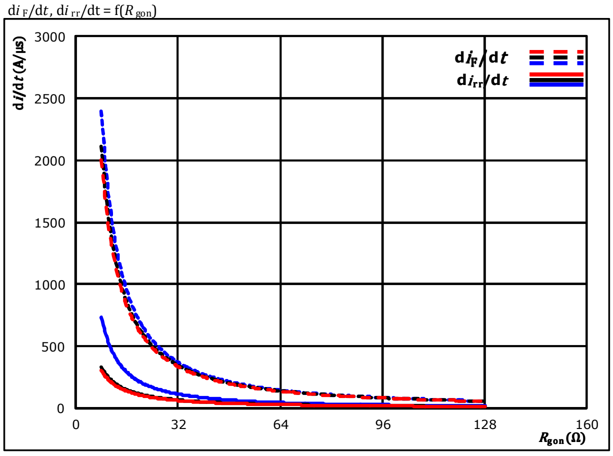
At V_{CE} = 600 V; V_{GE} = ±15 V; R_{gon} = 32 Ω

T_j: 25 °C (dotted), 125 °C (solid), 150 °C (dashed)

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



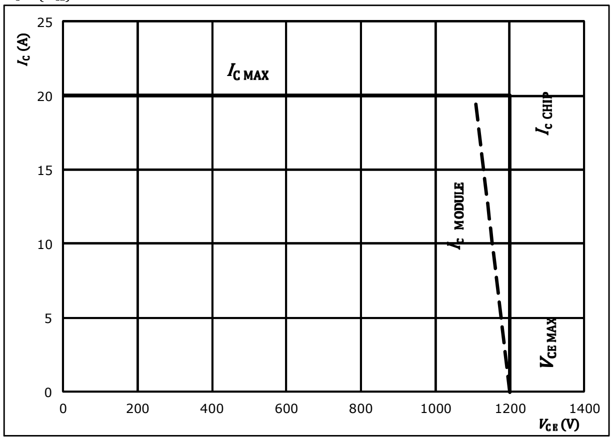
At V_{CE} = 600 V; V_{GE} = ±15 V; I_C = 10 A

T_j: 25 °C (dotted), 125 °C (solid), 150 °C (dashed)

figure 15. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At

T_j =	175	°C
R_{gon} =	32	Ω
R_{goff} =	32	Ω

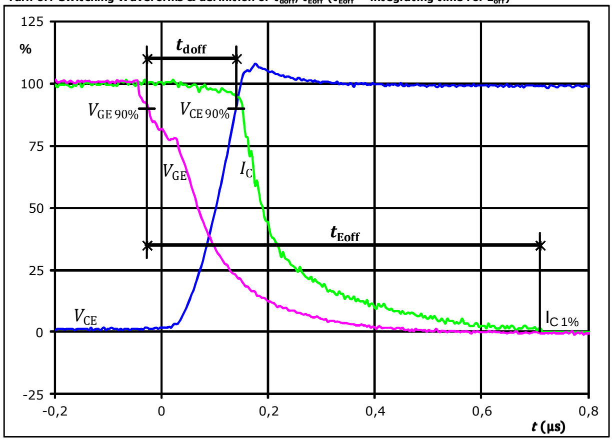
Inverter Switching Definitions

General conditions

T_j	=	125 °C
R_{gon}	=	32 Ω
R_{goff}	=	32 Ω

figure 1. **IGBT**

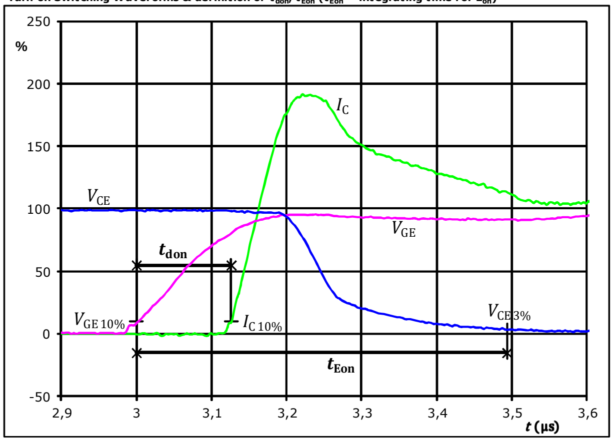
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{GE}(0\%)$ =	-15	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	10	A
t_{doff} =	0,179	µs
t_{Eoff} =	0,737	µs

figure 2. **IGBT**

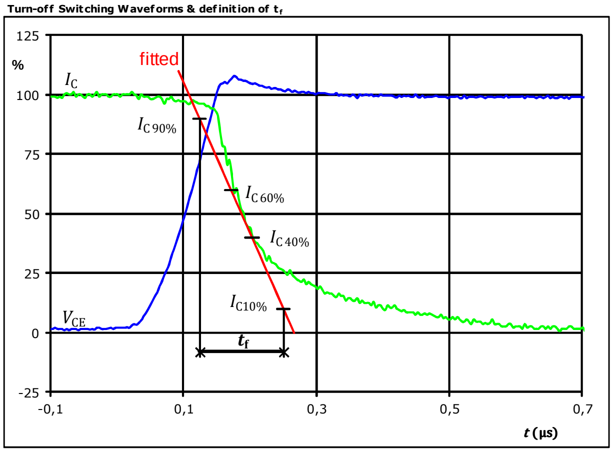
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{GE}(0\%)$ =	-15	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	10	A
t_{don} =	0,126	µs
t_{Eon} =	0,493	µs

figure 3. **IGBT**

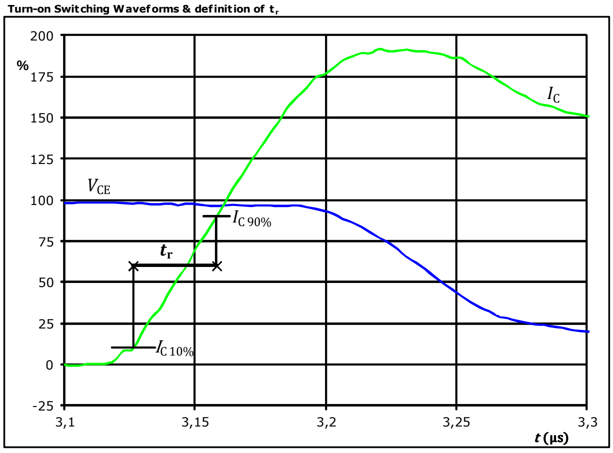
Turn-off Switching Waveforms & definition of t_f



$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	10	A
t_f =	0,108	µs

figure 4. **IGBT**

Turn-on Switching Waveforms & definition of t_r

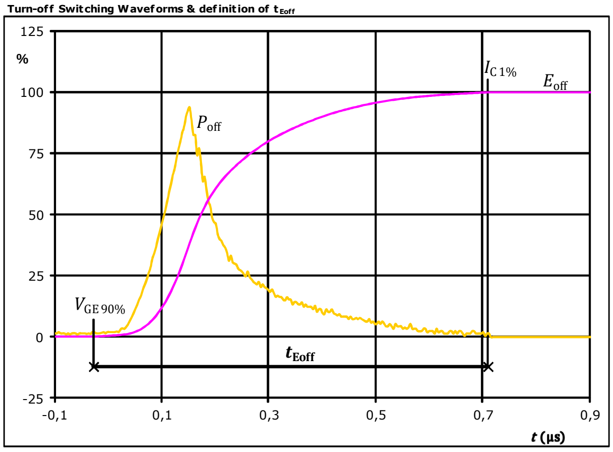


$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	10	A
t_r =	0,032	µs

Inverter Switching Characteristics

figure 5. **IGBT**

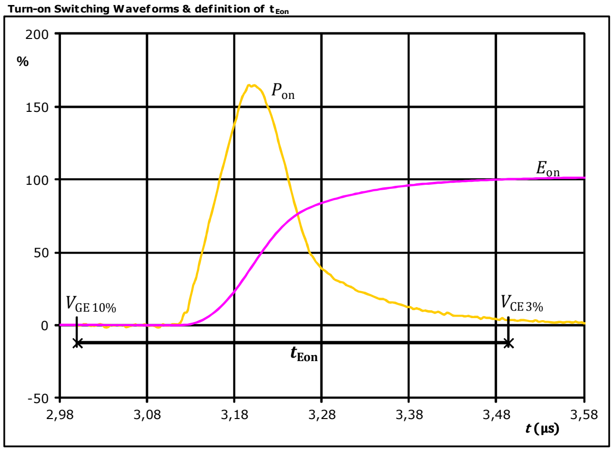
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) =	6,02	kW
E_{off} (100%) =	0,86	mJ
t_{Eoff} =	0,74	µs

figure 6. **IGBT**

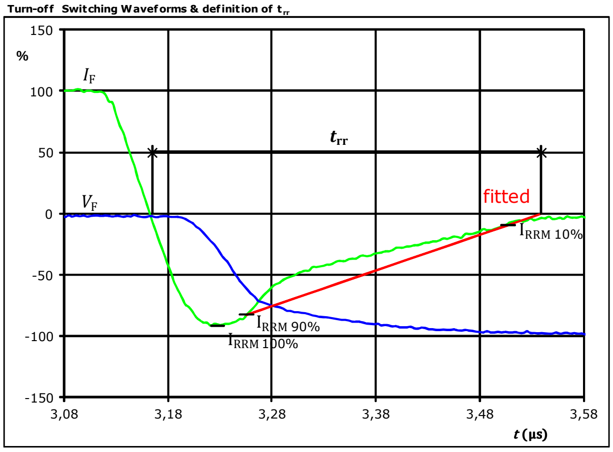
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) =	6,02	kW
E_{on} (100%) =	1,13	mJ
t_{Eon} =	0,49	µs

figure 7. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

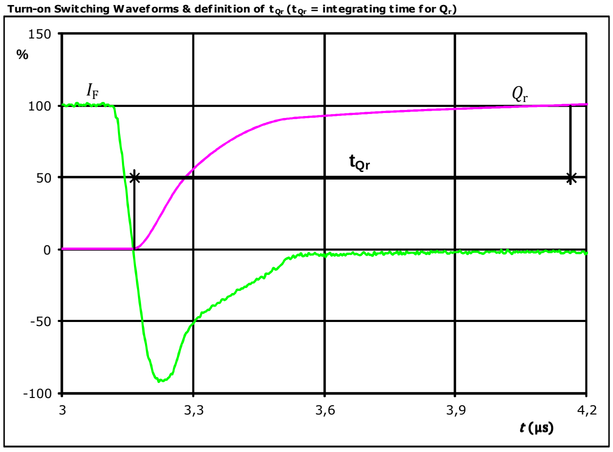


V_F (100%) =	600	V
I_F (100%) =	10	A
I_{RRM} (100%) =	-9	A
t_{rr} =	0,373	µs

Inverter Switching Characteristics

figure 8. **FWD**

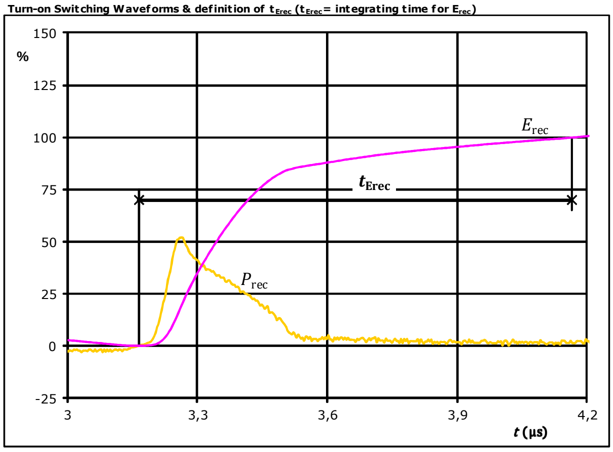
Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



I_F (100%) =	10	A
Q_r (100%) =	1,66	µC
t_{Qr} =	1,00	µs

figure 9. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec}= integrating time for E_{rec})



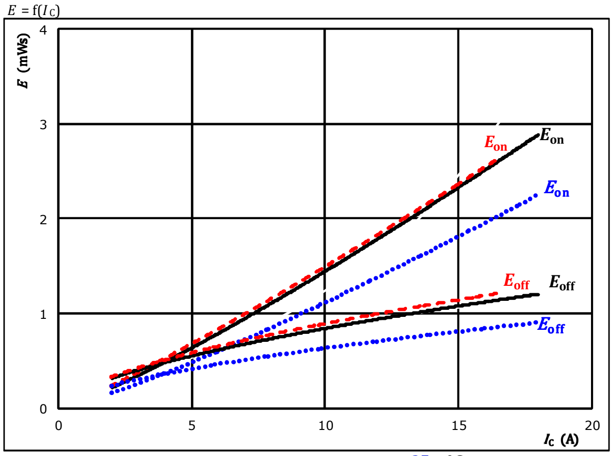
P_{rec} (100%) =	6,02	kW
E_{rec} (100%) =	0,62	mJ
t_{Erec} =	1,00	µs

Brake Switching Characteristics

figure 1. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



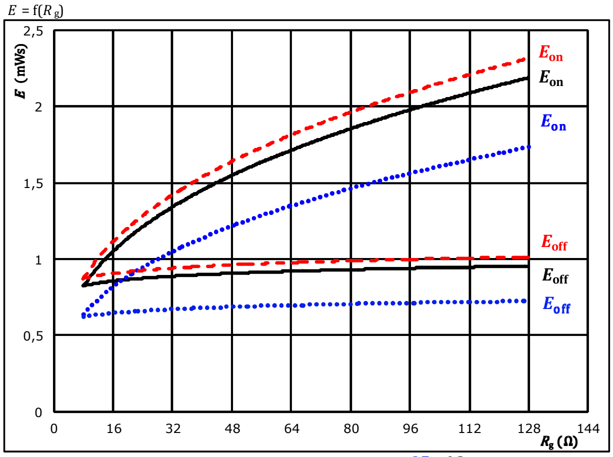
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	dotted
V_{GE} =	15/0	V		125 °C	solid
R_{gon} =	32	Ω		150 °C	dashed
R_{goff} =	32	Ω			

figure 2. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



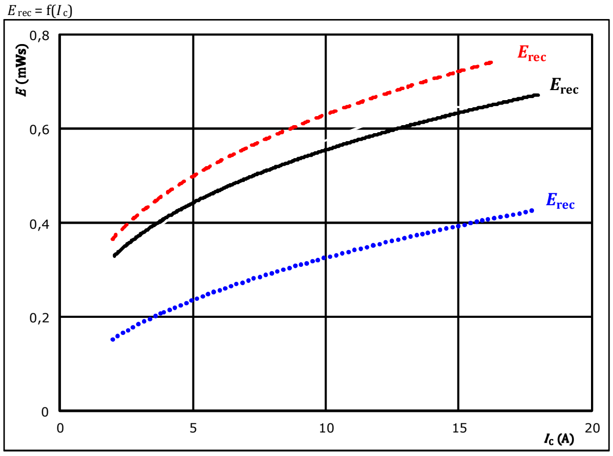
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	dotted
V_{GE} =	15/0	V		125 °C	solid
I_C =	10	A		150 °C	dashed

figure 3. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



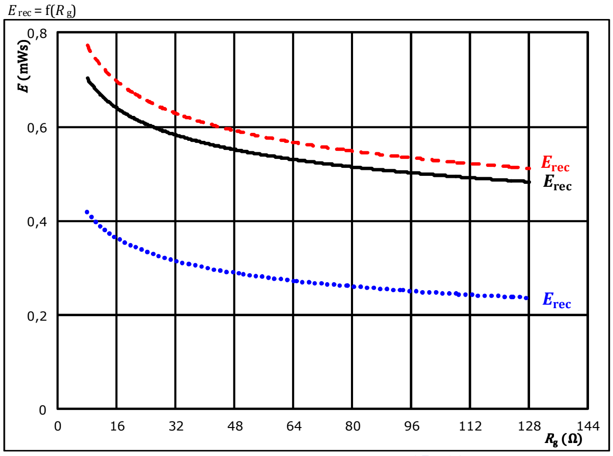
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	dotted
V_{GE} =	15/0	V		125 °C	solid
R_{gon} =	32	Ω		150 °C	dashed

figure 4. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

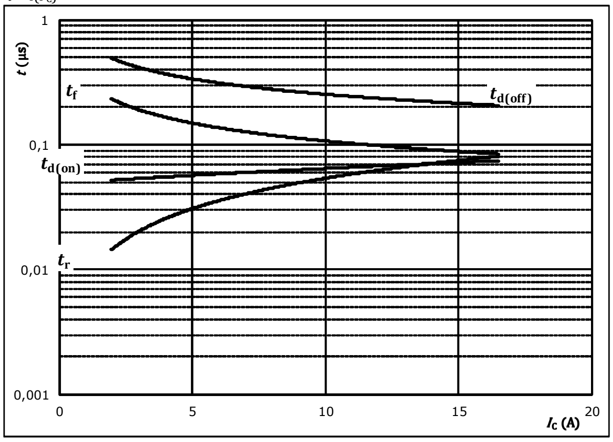
V_{CE} =	600	V	T_j:	25 °C	dotted
V_{GE} =	15/0	V		125 °C	solid
I_C =	10	A		150 °C	dashed

Brake Switching Characteristics

figure 5. IGBT

Typical switching times as a function of collector current

$t = f(I_C)$



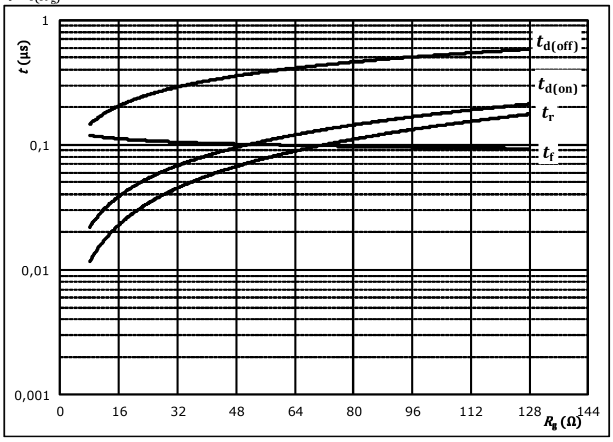
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	15/0	V
R_{gon} =	32	Ω
R_{goff} =	32	Ω

figure 6. IGBT

Typical switching times as a function of gate resistor

$t = f(R_g)$



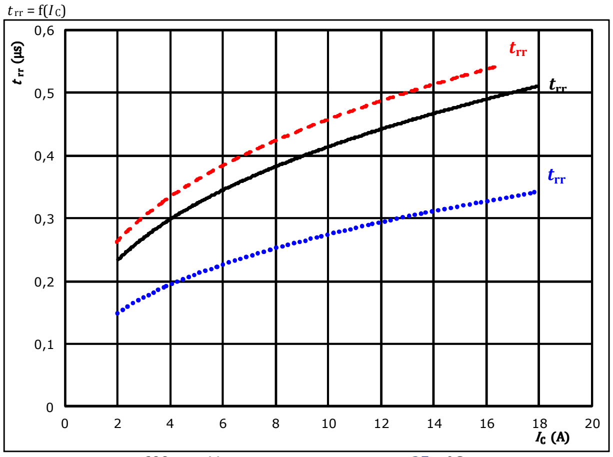
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	15/0	V
I_C =	10	A

figure 7. FWD

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$

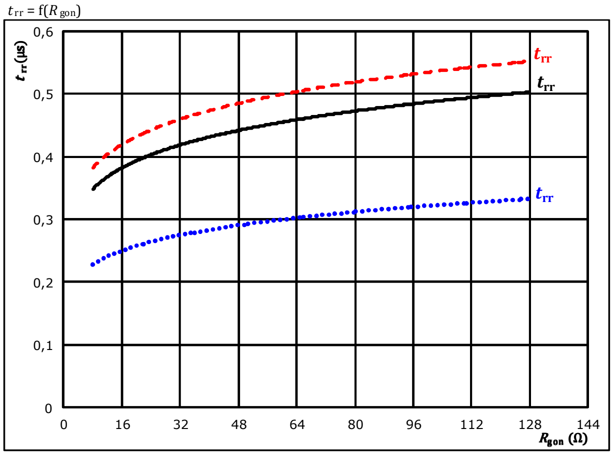


At					
V_{CE} =	600	V		25	°C
V_{GE} =	15/0	V	T_j:	125	°C
R_{gon} =	32	Ω		150	°C

figure 8. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



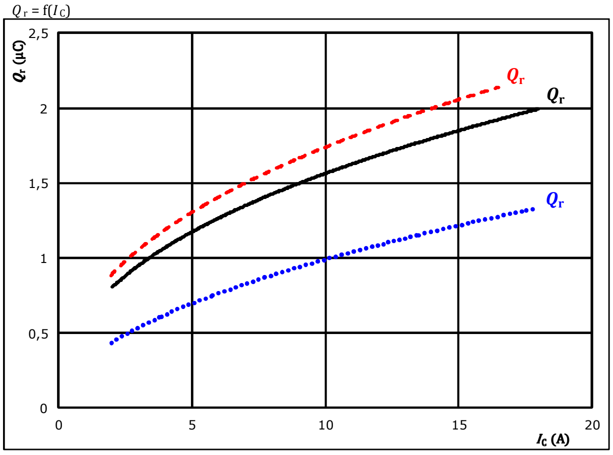
At					
V_{CE} =	600	V		25	°C
V_{GE} =	15/0	V	T_j:	125	°C
I_C =	10	A		150	°C

Brake Switching Characteristics

figure 9. **FWD**

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$

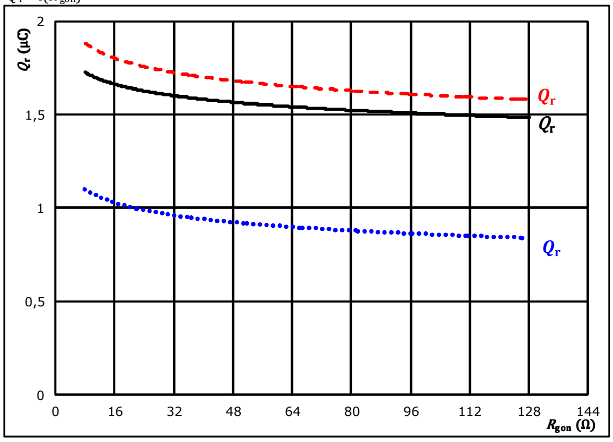


At						
	V_{CE} =	600	V		25 °C	············
	V_{GE} =	15/0	V	T_j:	125 °C	———
	R_{gon} =	32	Ω		150 °C	– – –

figure 10. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$

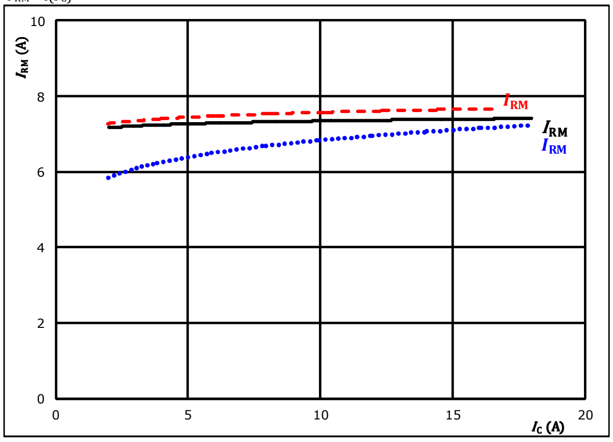


At						
	V_{CE} =	600	V		25 °C	············
	V_{GE} =	15/0	V	T_j:	125 °C	———
	I_C =	10	A		150 °C	– – –

figure 11. **FWD**

Typical peak reverse recovery current current as a function of collector current

$I_{RM} = f(I_C)$

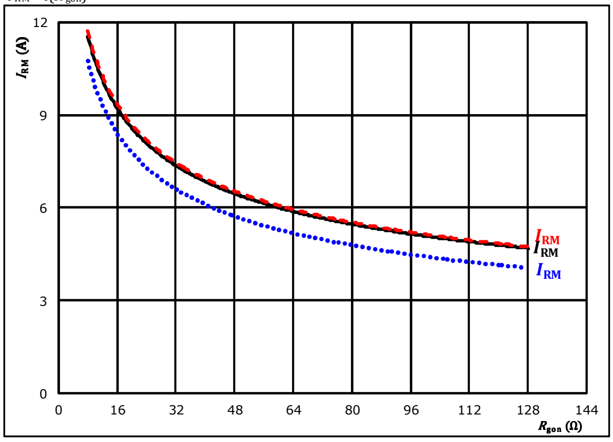


At						
	V_{CE}:	600	V		25 °C	············
	V_{GE} =	15/0	V	T_j:	125 °C	———
	R_{gon} =	32	Ω		150 °C	– – –

figure 12. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



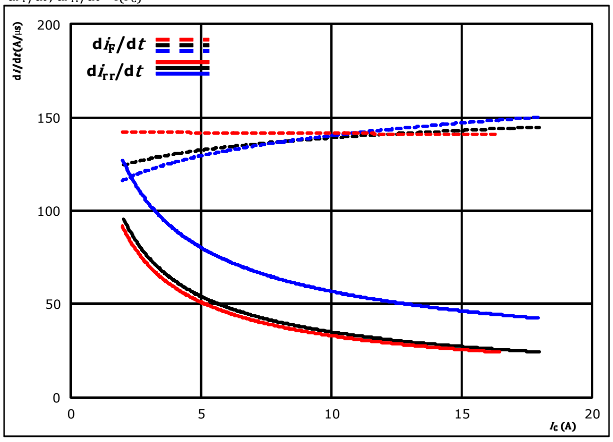
At						
	V_{CE} =	600	V		25 °C	············
	V_{GE} =	15/0	V	T_j:	125 °C	———
	I_C =	10	A		150 °C	– – –

Brake Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



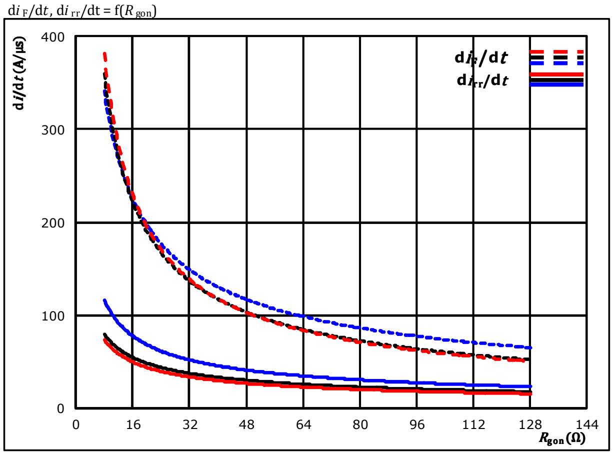
At

V_{CE} =	600	V		25	°C	dotted
V_{GE} =	15/0	V	T_j:	125	°C	solid
R_{gon} =	32	Ω		150	°C	dashed

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



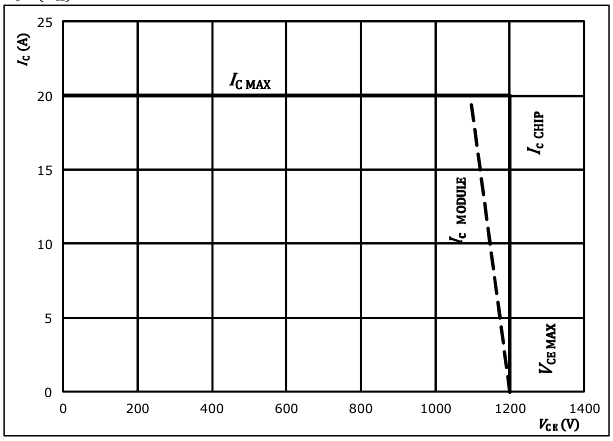
At

V_{CE} =	600	V		25	°C	dotted
V_{GE} =	15/0	V	T_j:	125	°C	solid
I_C=	10	A		150	°C	dashed

figure 15. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At

T_j =	175	°C
R_{gon} =	32	Ω
R_{goff} =	32	Ω

Vincotech

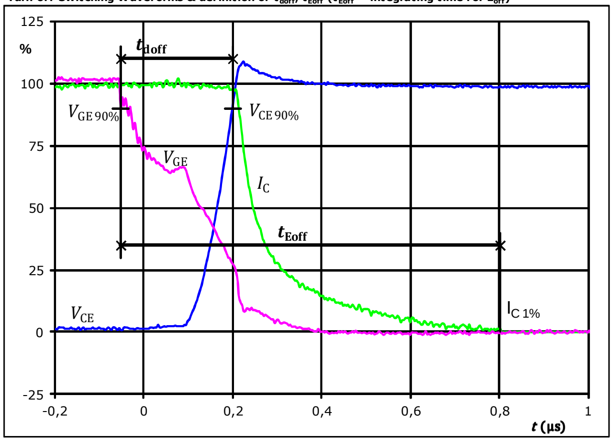
Brake Switching Definitions

General conditions

T_j	=	125 °C
R_{gon}	=	32 Ω
R_{goff}	=	32 Ω

figure 1. **IGBT**

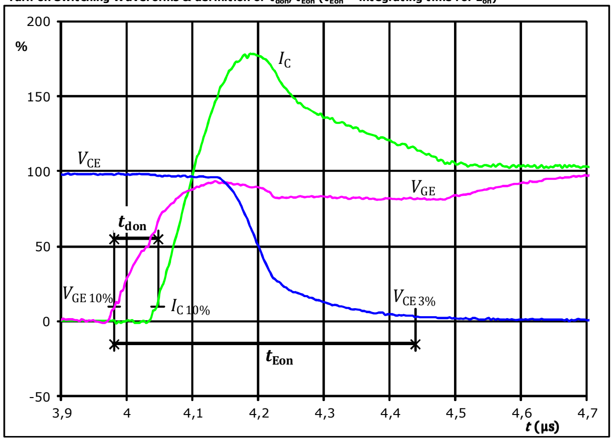
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{GE}(0\%)$ =	0	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	10	A
t_{doff} =	0,251	µs
t_{Eoff} =	0,853	µs

figure 2. **IGBT**

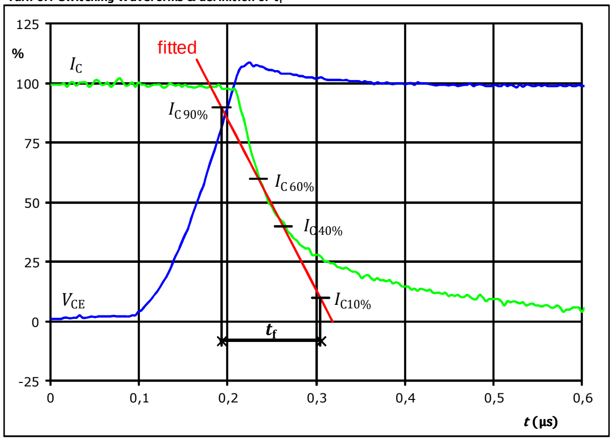
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{GE}(0\%)$ =	0	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	10	A
t_{don} =	0,068	µs
t_{Eon} =	0,458	µs

figure 3. **IGBT**

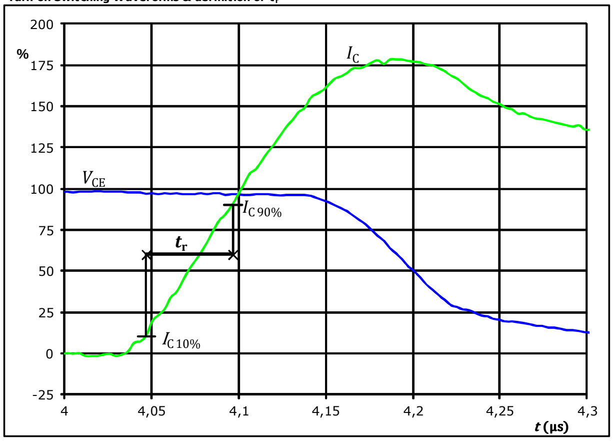
Turn-off Switching Waveforms & definition of t_f



$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	10	A
t_f =	0,111	µs

figure 4. **IGBT**

Turn-on Switching Waveforms & definition of t_r

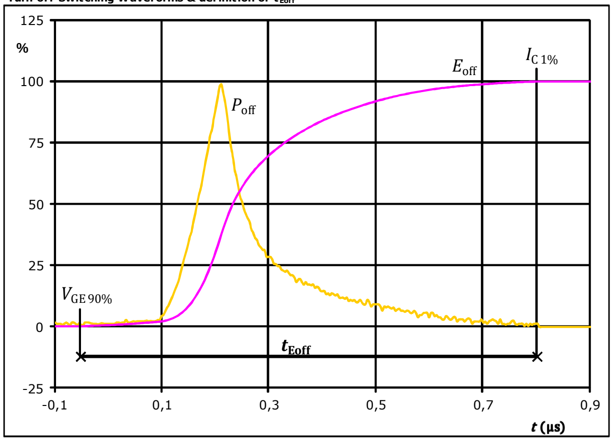


$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	10	A
t_r =	0,050	µs

Brake Switching Characteristics

figure 5. **IGBT**

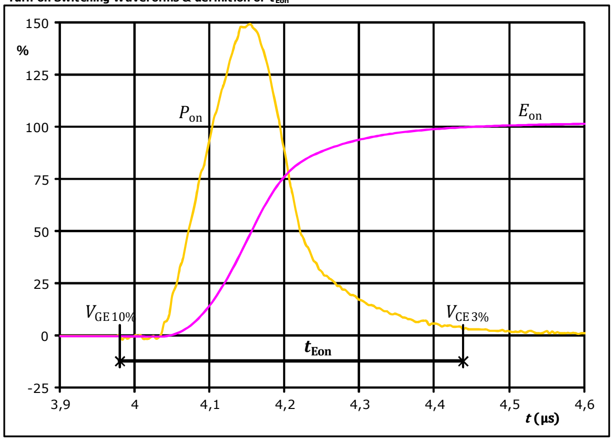
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) =	6,03	kW
E_{off} (100%) =	0,86	mJ
t_{Eoff} =	0,85	µs

figure 6. **IGBT**

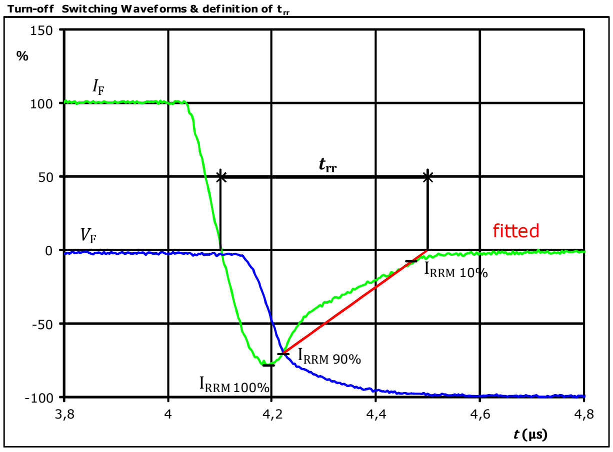
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) =	6,03	kW
E_{on} (100%) =	1,25	mJ
t_{Eon} =	0,46	µs

figure 7. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

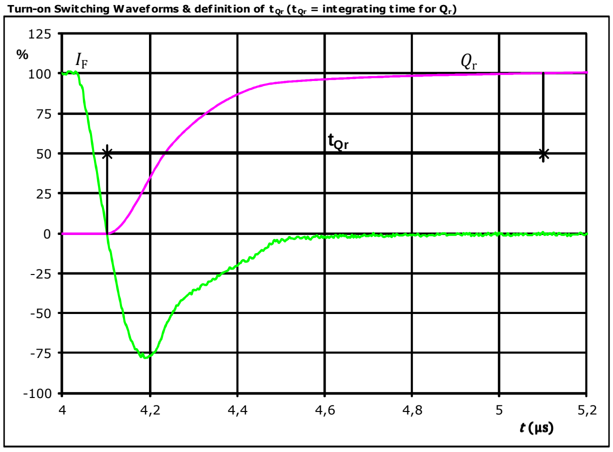


V_F (100%) =	600	V
I_F (100%) =	10	A
I_{RRM} (100%) =	-8	A
t_{rr} =	0,396	µs

Brake Switching Characteristics

figure 8. **FWD**

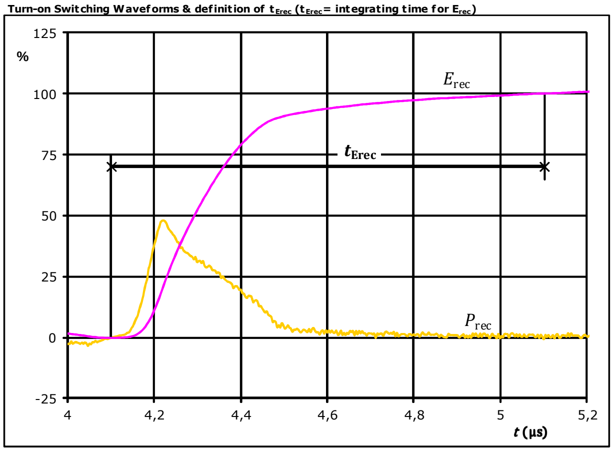
Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



I_F (100%) =	10	A
Q_r (100%) =	1,57	µC
t_{Qr} =	1,00	µs

figure 9. **FWD**

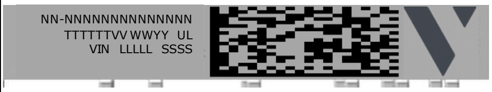
Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



P_{rec} (100%) =	6,03	kW
E_{rec} (100%) =	0,58	mJ
t_{Erec} =	1,00	µs

Ordering Code & Marking

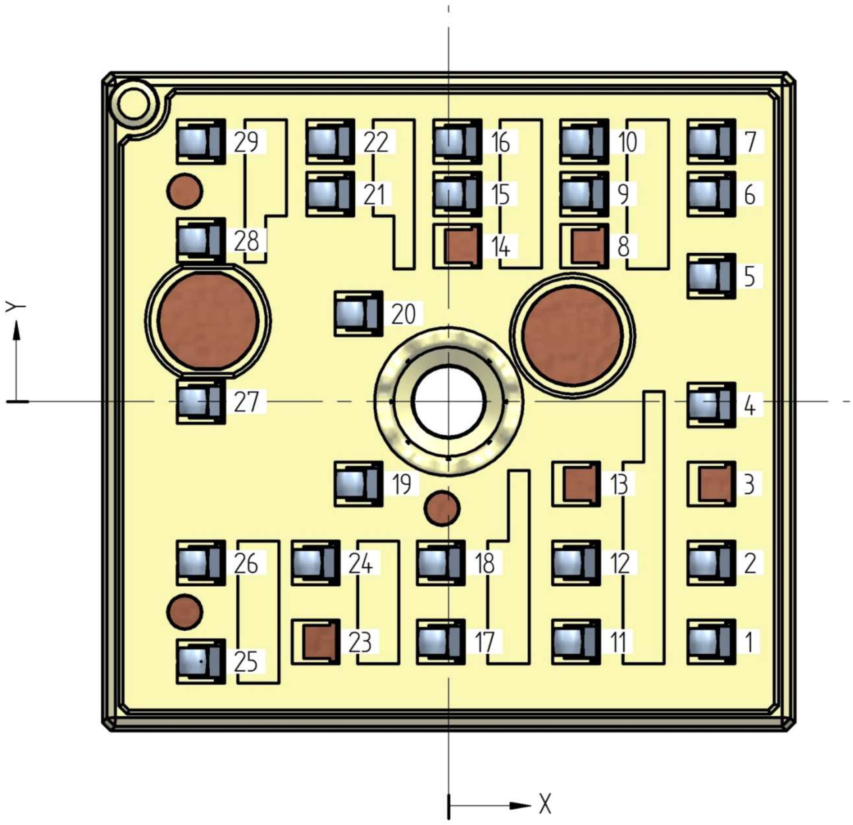
Version	Ordering Code
With std lid (6.5mm height) + no thermal grease	80-M112PMA010M7-K209A70-/0A/
With thin lid (2.8mm height) + no thermal grease	80-M112PMA010M7-K209A70-/0B/
With std lid (6.5mm height) + thermal grease (0,8 W/mK, P12, silicone-based)	80-M112PMA010M7-K209A70-/1A/
With thin lid (2.8mm height) + thermal grease (0,8 W/mK, P12, silicone-based)	80-M112PMA010M7-K209A70-/1B/
With std lid (6.5mm height) + thermal grease (2,5 W/mK, TG20032, silicone-free)	80-M112PMA010M7-K209A70-/4A/
With thin lid (2.8mm height) + thermal grease (2,5 W/mK, TG20032, silicone-free)	80-M112PMA010M7-K209A70-/4B/
With std lid (6.5mm height) + thermal grease (2,5 W/mK, HPTP, silicone-based)	80-M112PMA010M7-K209A70-/5A/
With thin lid (2.8mm height) + thermal grease (2,5 W/mK, HPTP, silicone-based)	80-M112PMA010M7-K209A70-/5B/



Text	Name		Date code	UL & VIN	Lot	Serial
	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	Type&Ver	Lot number	Serial	Date code		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

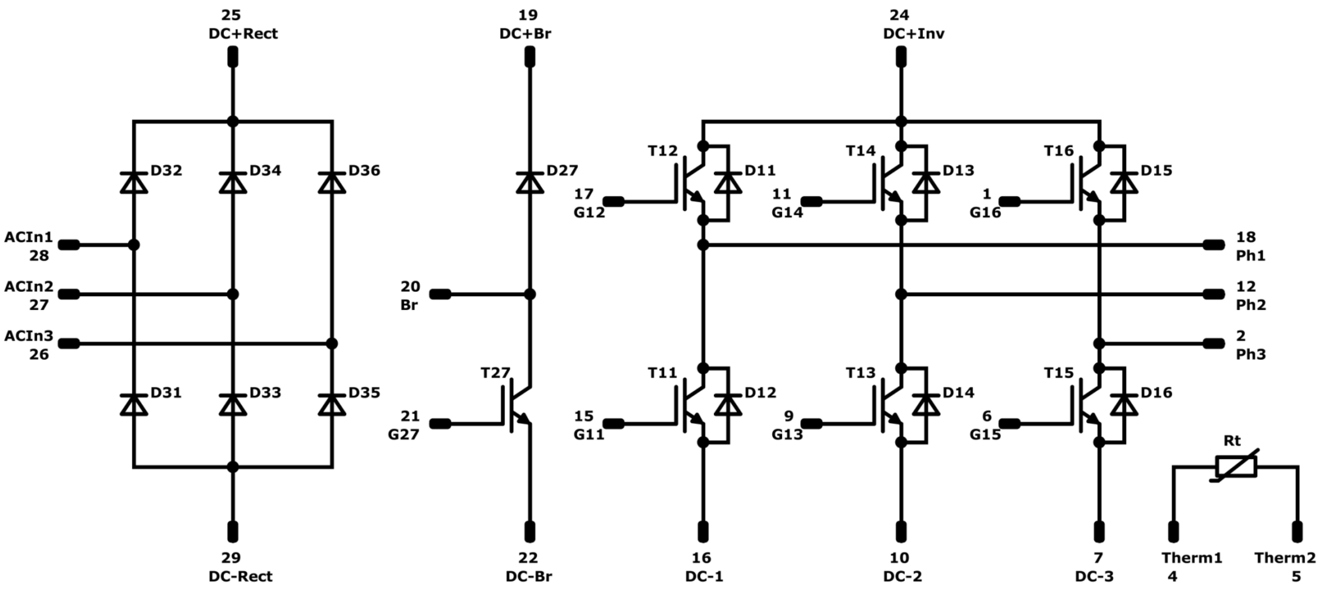
Outline

PCB pad table			
Pin	X	Y	Function
1	15,93	-14,6	G16
2	15,93	-9,8	Ph3
3	Not assembled		
4	15,93	-0,2	Therm1
5	15,93	7,62	Therm2
6	15,93	12,62	G15
7	15,93	15,8	DC-3
8	Not assembled		
9	8,23	12,62	G13
10	8,23	15,8	DC-2
11	7,73	-14,6	G14
12	7,73	-9,8	Ph2
13	Not assembled		
14	Not assembled		
15	0,53	12,62	G11
16	0,53	15,8	DC-1
17	-0,47	-14,6	G12
18	-0,47	-9,8	Ph1
19	-5,47	-5	DC+Br
20	-5,47	5,35	Br
21	-7,17	12,62	G27
22	-7,17	15,8	DC-Br
23	Not assembled		
24	-8,07	-9,8	DC+Inv
25	-15,02	-15,8	DC+Rect
26	-15,02	-9,8	ACIn3
27	-15,02	0	ACIn2
28	-15,02	9,8	ACIn1
29	-15,02	15,8	DC-Rect



Pad positions refers to center point. For more informations on pad design please see package data

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
D31 , D32 , D33 , D34 , D35 , D36	Rectifier	1600 V	25 A	Rectifier Diode	
T11 , T12 , T13 , T14 , T15 , T16	IGBT	1200 V	10 A	Inverter Switch	
D11 , D12 , D13 , D14 , D15 , D16	FWD	1200 V	10 A	Inverter Diode	
T27	IGBT	1200 V	10 A	Brake Switch	
D27	FWD	1200 V	10 A	Brake Diode	
Rt	PTC			Thermistor	

Vincotech

80-M112PMA010M7-K209A70
datasheet

Packaging instruction				
Standard packaging quantity (SPQ) 120	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for MiniSkiiP® 1 packages see vincotech.com website.

Package data
Package data for MiniSkiiP® 1 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
80-M112PMA010M7-K209A70-D1-14	27 Oct. 2017		